SILICON EPITAXIAL PLANAR DIODE

Applications

Ultra high speed switching





SOT-323 Plastic Package Marking Code: **PH**

Absolute Maximum Ratings (T_a = 25 °C)

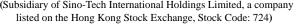
Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Average Forward Current	Ι _Ο	100	mA
Maximum (Peak) Forward Current	I _{FM}	300	mA
Peak Forward Surge Current (t _p = 10 ms)	I _{FSM}	2	А
Total Power Dissipation	P _{tot}	200	mW
Junction Temperature	TJ	125	°C
Storage Temperature Range	Ts	- 55 to + 125	°C

Characteristics at $T_a = 25 \ ^{\circ}C$

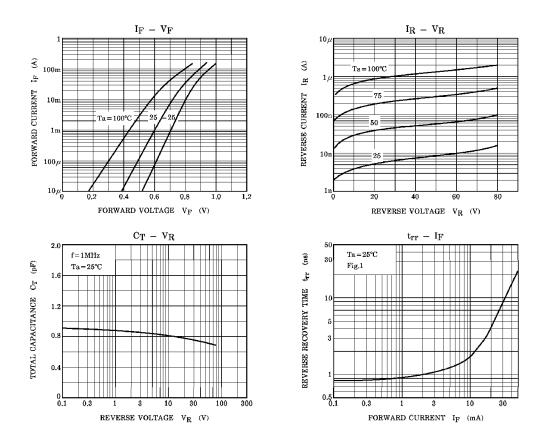
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	-	1.2	V
Reverse Current at $V_R = 30 V$ at $V_R = 80 V$	I _R	-	0.1 0.5	μΑ
Total Capacitance at $V_R = 0$, f = 1 MHz	C _T	-	3	pF
Reverse Recovery Time at I _F = 10 mA, V _R = 6 V, I _{rr} = 1 mA, R _L = 100 Ω	t _{rr}	-	4	ns















(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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